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Via Fax Only

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Examiner Ortiz

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Message

United States Patent Application No.: 09/890,120

Filed: July 27, 2001

Title: Dynamic Threshold Voltage MOS Transistor Fitted with a Current Limiter, and Processor for Making Such a Transistor

Inventors: Pelloie, et al.

Reference No.: 034299-336

Please find the attached Preliminary Amendment for the above reference application.

Docket No. 034299-336

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Jean-Luc Pelloie
SERIAL NO.: 09/890,120
FILING DATE: July 27, 2001
TITLE: DYNAMIC THRESHOLD VOLTAGE MOS TRANSISTOR
FITTED WITH A CURRENT LIMITER, AND PROCESS FOR
MAKING SUCH A TRANSISTOR
EXAMINER: Edgardo, Ortiz
ART UNIT: 2815

#12/E
PRE-Amend
J. Meimle
12/21/02

PRELIMINARY AMENDMENT

Prior to examination, please amend the subject patent application as follows:

IN THE CLAIMS:

Please amend the claims as follows, the amendments which are shown in the
attached VERSION WITH MARKINGS TO SHOW CHANGES MADE.

1. (Once Amended) A semiconductor device formed on a substrate,
comprising:
a first dynamic threshold voltage MOS transistor having a gate and a channel of a
first conductivity type;

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